优尚

YOUSHANG SEMICONDUCTOR

设计研发新型功率器件

各类小信号开关

中低压及高压大电流等场效应管

0755-83047638
ysbdt@szyoushang.cn
www.szyoushang.cn

企业微信二维码

企业QQ二维码

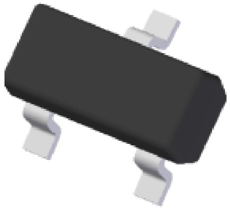
Features

- Epitaxial Planar Die Construction
- Ideal for Low Power Amplification and Switching
- Complementary NPN Type: NK-MMBTA05 / NK-MMBTA06

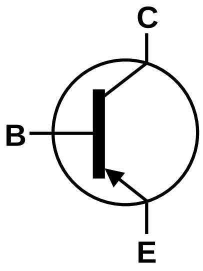
Mechanical Data

- Package: SOT23
- Package Material: Molded Plastic, “Green” Molding Compound; UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish-Matte Tin Plated Leads. Solderable per MIL-STD-202, Method 208 e3
- Weight: 0.008 grams (Approximate)

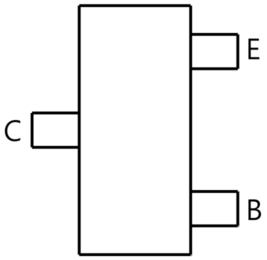
SOT23



Top View



Device Symbol



Top View
Pin-Out

Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	MMBTA55	MMBTA56	Unit
Collector-Base Voltage	V_{CBO}	-60	-80	V
Collector-Emitter Voltage	V_{CEO}	-60	-80	V
Emitter-Base Voltage	V_{EBO}	-4.0		V
Collector Current - Continuous	I_C	-500		mA

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Power Dissipation	(Note 5)	P_D	310	mW
	(Note 6)		350	
Thermal Resistance, Junction to Ambient	(Note 5)	$R_{\theta JA}$	403	°C/W
	(Note 6)		357	
Thermal Resistance, Junction to Leads	(Note 7)	$R_{\theta JL}$	350	°C/W
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +150	°C

ESD Ratings (Note 8)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	C

Notes:

5. For a device mounted on minimum recommended pad layout 1oz copper that is on a single-sided FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.
6. Same as Note 5, except the device is mounted on 15 mm x 15mm 1oz copper.
7. Thermal resistance from junction to solder-point (at the end of the leads).
8. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

Thermal Characteristics and Derating Information

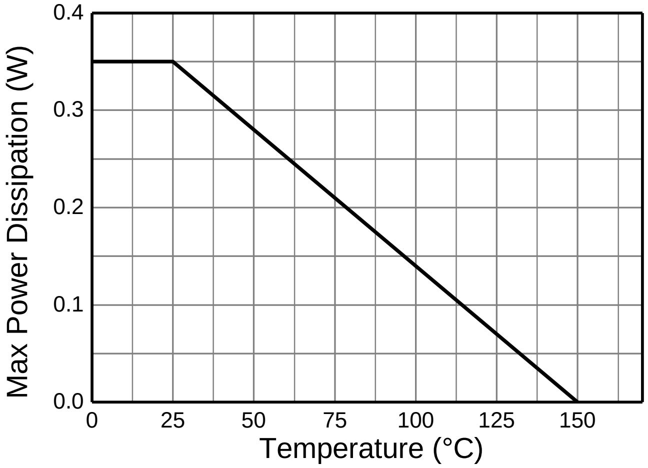


Figure 1. Derating Curve

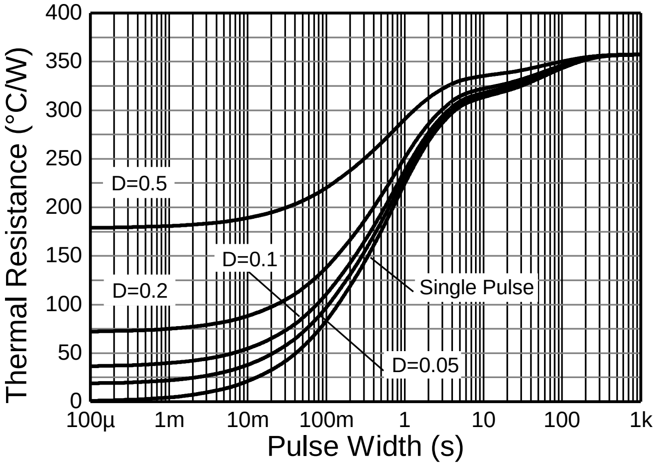


Figure 2. Transient Thermal Impedance

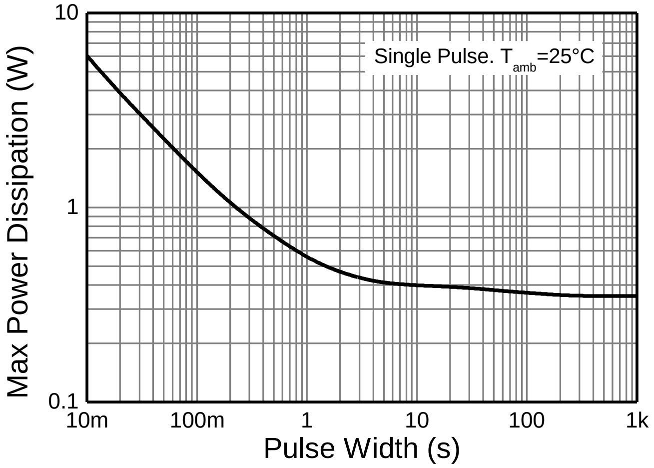


Figure 3. Pulse Power Dissipation

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 9)						
Collector-Base Breakdown Voltage	NK-MMBTA55 NK-MMBTA56	BV_{CBO}	-60 -80	—	V	I_C = -100µA, I_E = 0
Collector-Emitter Breakdown Voltage	NK-MMBTA55 NK-MMBTA56	BV_{CEO}	-60 -80	—	V	I_C = -1.0mA, I_B = 0
Emitter-Base Breakdown Voltage		BV_{EBO}	-5.0	-4.0	—	I_E = -100µA, I_C = 0
Collector Cut-Off Current	NK-MMBTA55 NK-MMBTA56	I_{CBO}	—	-100	nA	V_{CB} = -60V, I_E = 0 V_{CB} = -80V, I_E = 0
Collector Cut-Off Current	NK-MMBTA55 NK-MMBTA56	I_{CEX}	—	-100	nA	V_{CE} = -60V, I_{BO} = 0V V_{CE} = -80V, I_{BO} = 0V
ON CHARACTERISTICS (Note 9)						
DC Current Gain		h_{FE}	100	—	—	I_C = -10mA, V_{CE} = -1.0V I_C = -100mA, V_{CE} = -1.0V
Collector-Emitter Saturation Voltage		$V_{CE(sat)}$	—	-0.25	V	I_C = -100mA, I_B = -10mA
Base-Emitter Saturation Voltage		$V_{BE(sat)}$	—	-1.2	V	I_C = -100mA, V_{CE} = -1.0V
SMALL SIGNAL CHARACTERISTICS						
Current Gain-Bandwidth Product		f_T	50	—	MHz	V_{CE} = -1.0V, I_C = -100mA, f = 100MHz

Note: 9. Measured under pulsed conditions. Pulse width ≤ 300µs. Duty cycle ≤ 2%.

Typical Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

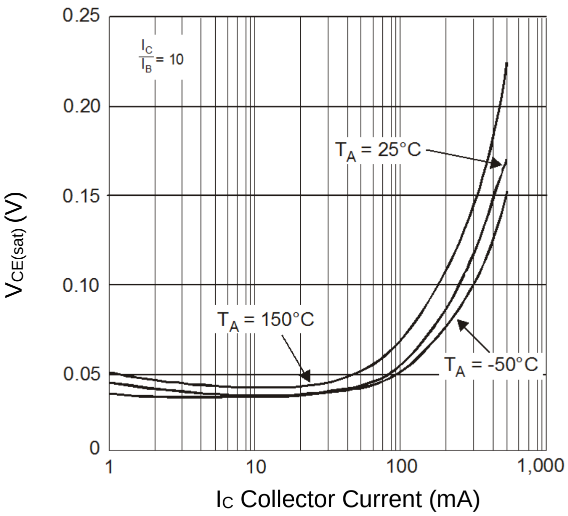


Figure 4. V_{CE} v I_C

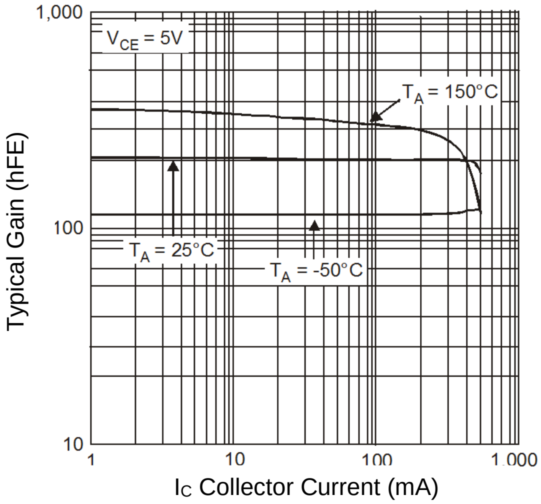


Figure 5. h_{FE} v I_C

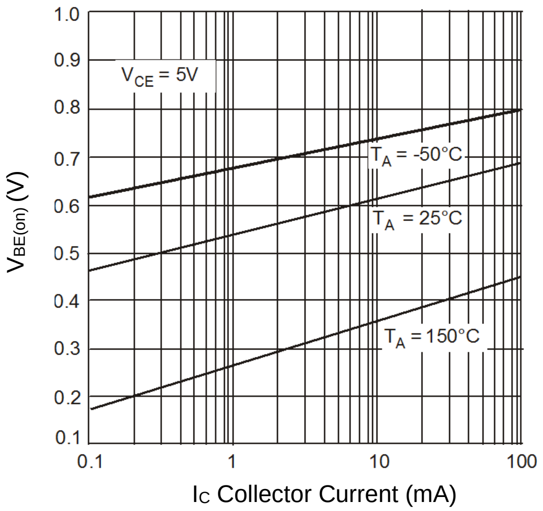


Figure 6. $V_{BE(on)}$ v I_C

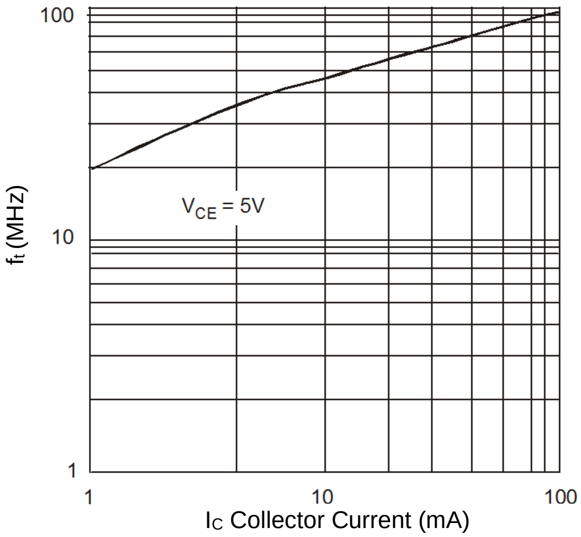
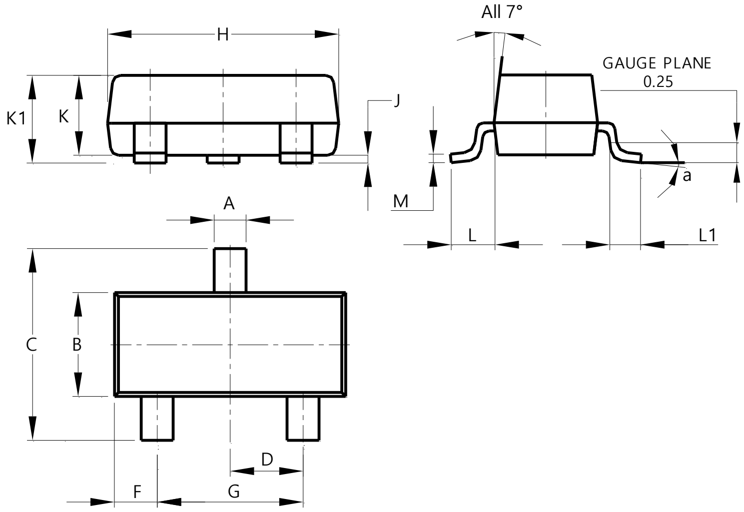


Figure 7. f_t v I_C

Package Outline Dimensions

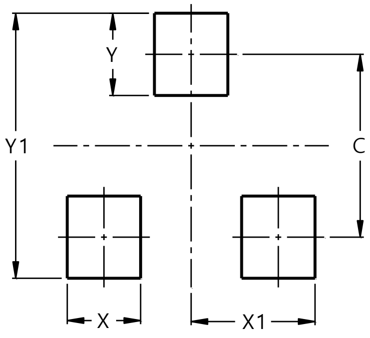
SOT23



SOT23			
Dim	**Min**	**Max**	**Typ**
A	0.37	0.51	0.40
B	1.20	1.40	1.30
C	2.30	2.50	2.40
D	0.89	1.03	0.915
F	0.45	0.60	0.535
G	1.78	2.05	1.83
H	2.80	3.00	2.90
J	0.013	0.10	0.05
K	0.890	1.00	0.975
K1	0.903	1.10	1.025
L	0.45	0.61	0.55
L1	0.25	0.55	0.40
M	0.085	0.150	0.110
a	0°	8°	--
All Dimensions in mm			

Suggested Pad Layout

SOT23



Dimensions	Value (in mm)
C	2.0
X	0.8
X1	1.35
Y	0.9
Y1	2.9